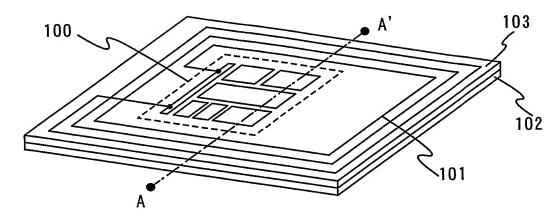
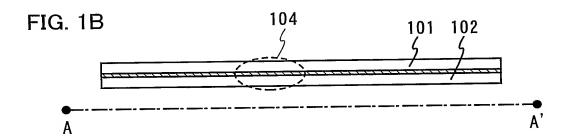
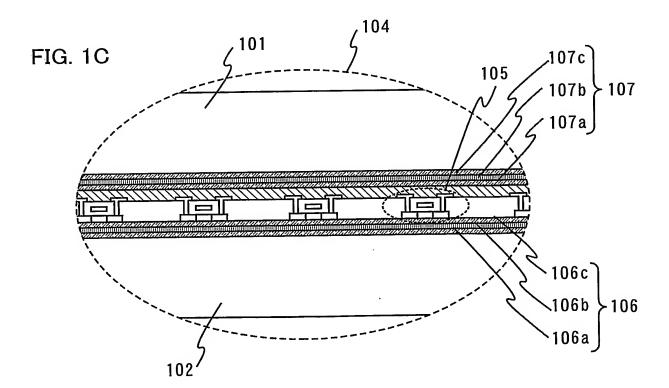


FIG. 1A









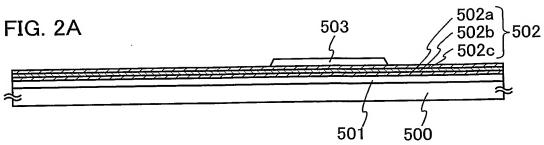
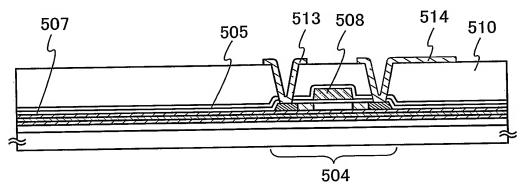


FIG. 2B



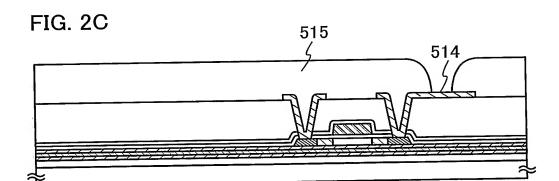
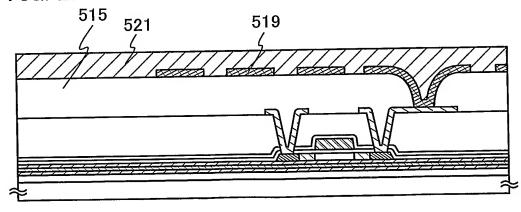
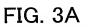


FIG. 2D







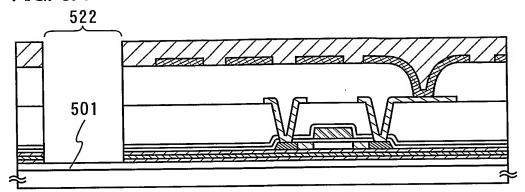
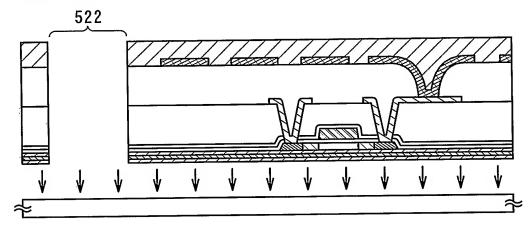
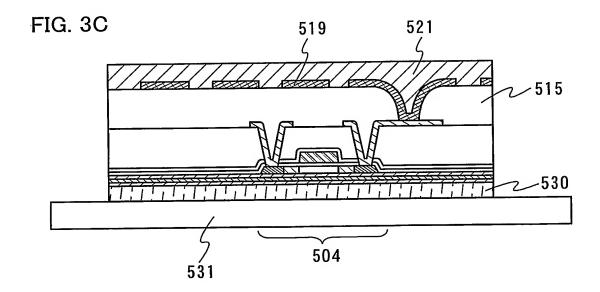
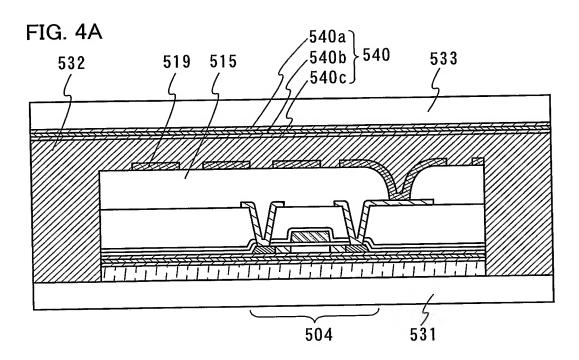


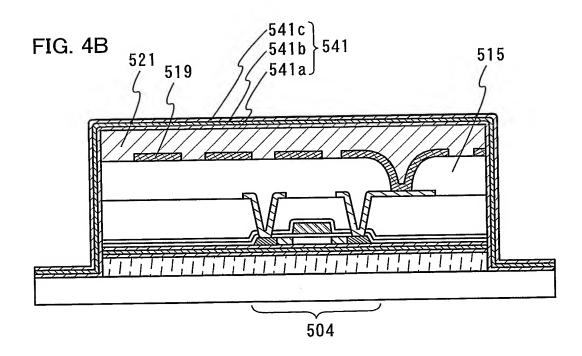
FIG. 3B



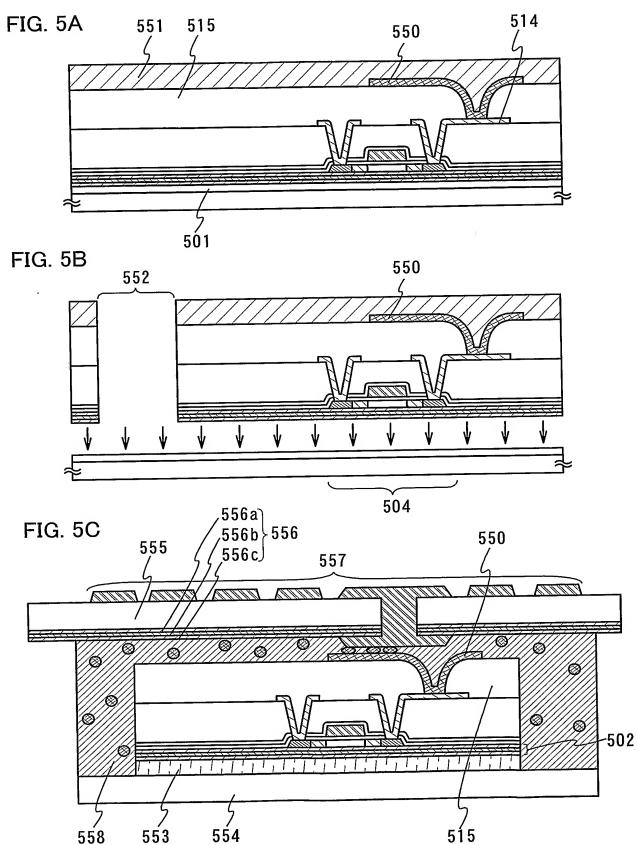












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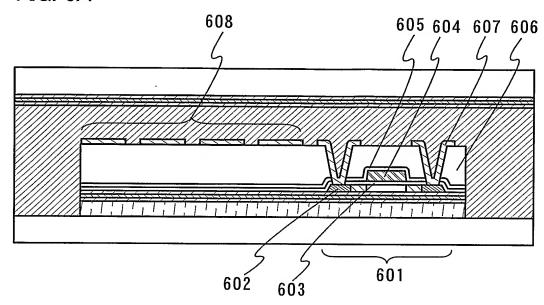
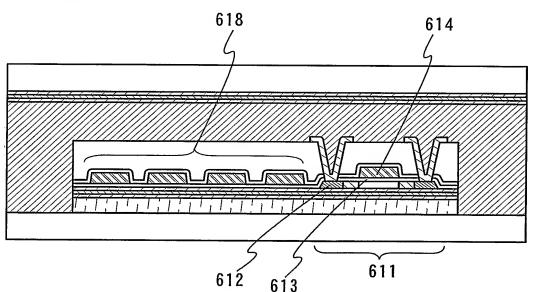
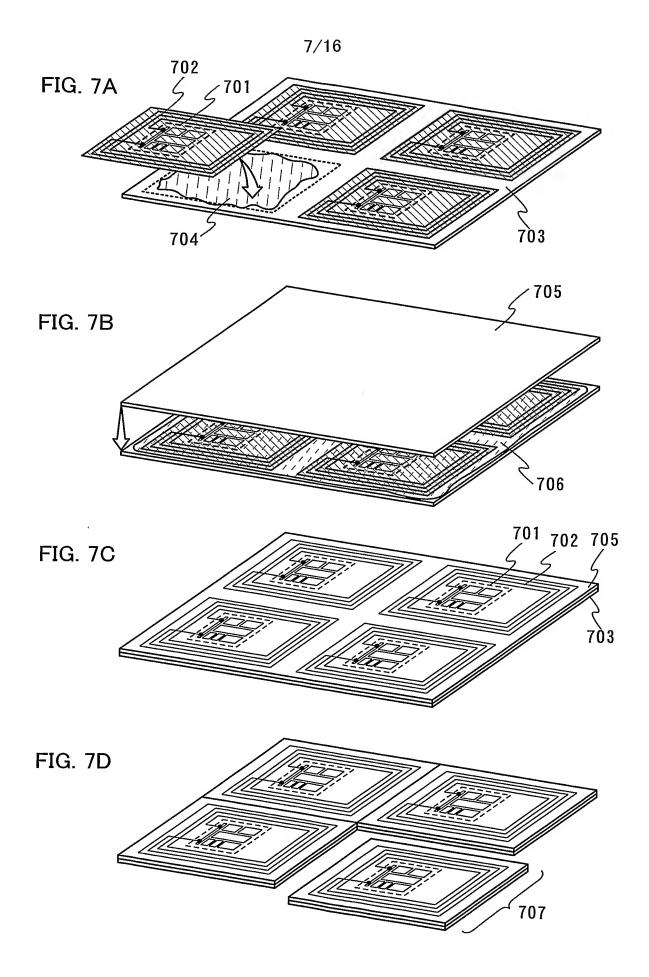


FIG. 6B





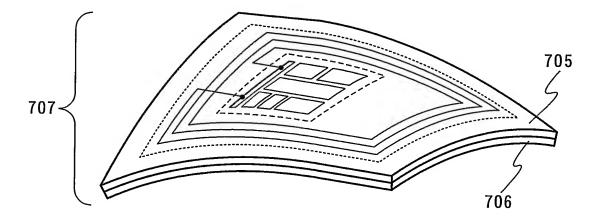


FIG. 8

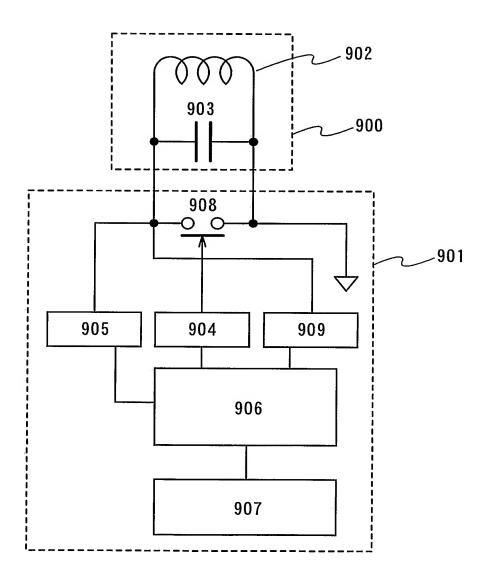
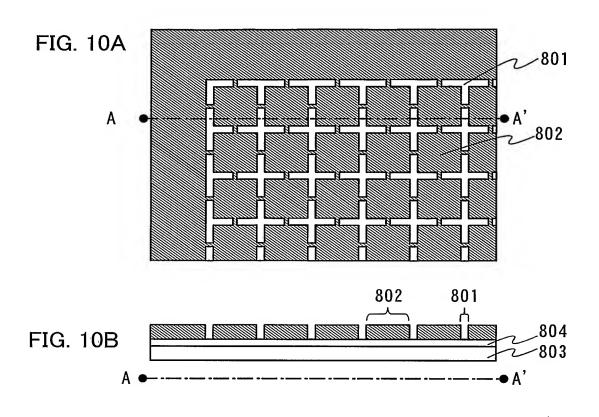
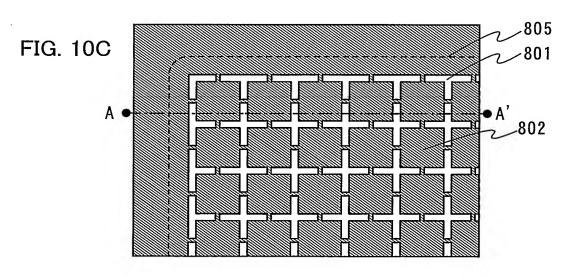


FIG. 9





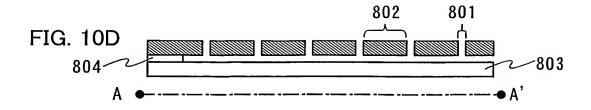


FIG. 11A

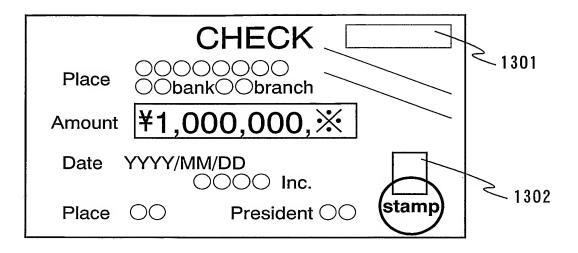


FIG. 11B

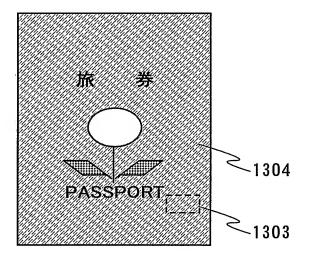
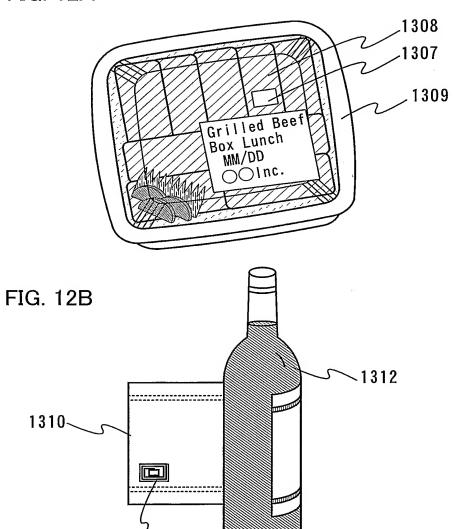


FIG. 11C

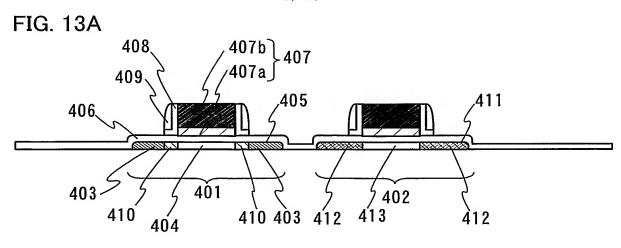


FIG. 12A

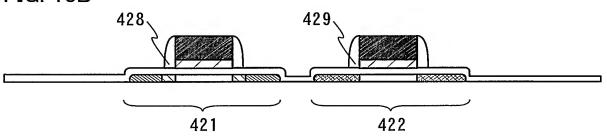


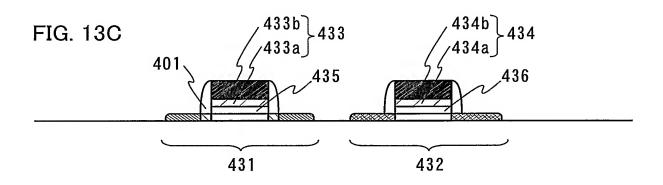
1311

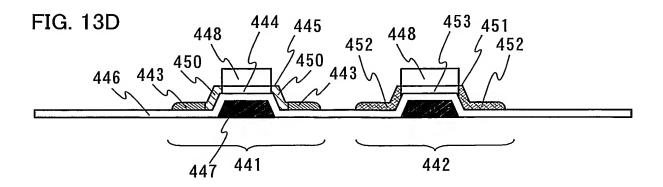












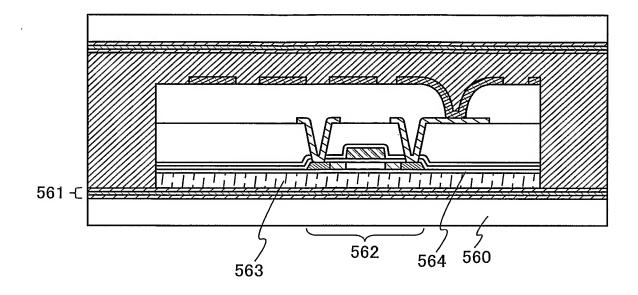


FIG. 14

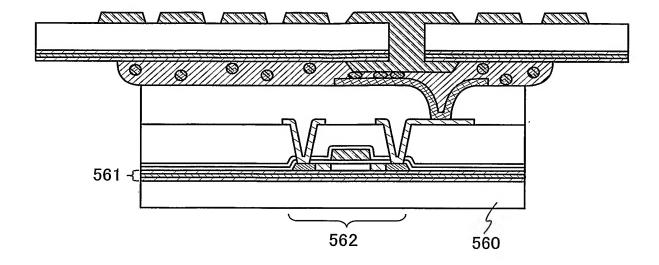


FIG. 15

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EXPLANATION OF REFERENCE

100: integrated circuit, 101: antenna, 102: substrate, 103: cover member, 104: dashed line, 105: TFT, 106: sealing film, 106a: barrier film, 106b: stress relaxation film, 106c: barrier film, 107: sealing film, 107a: barrier film, 107b: stress relaxation film, 107c: barrier film, 1301: check, 1302: ID chip, 1303: ID chip, 1304: passport, 1305: ID chip, 1306: token, 1307: ID chip, 1308: packing material, 1309: boxed meal, 1310: label, 1311: ID chip, 1312: commercial product, 401: n-channel TFT, 402: p-channel TFT, 403: impurity region, 404: channel formation region, 405: active layer, 406: gate insulating film, 407: gate electrode, 407a: conductive film, 407b: conductive film, 408: sidewall, 409: sidewall, 410: LDD region, 411: active region, 412: impurity region, 413: channel formation region, 421: n-channel TFT, 422: p-channel TFT, 428: sidewall, 429: sidewall, 431: n-channel TFT, 432: p-channel TFT, 433: gate electrode, 433a: conductive film, 433b: conductive film, 434: gate electrode, 434a: conductive film, 434b: conductive film, 435: gate insulating film, 436: gate insulating film, 441: n-channel TFT, 442: p-channel TFT, 443: impurity region, 444: channel formation region, 445: active layer, 446: gate insulating film, 447: gate electrode, 448: protective film, 450: LDD region, 451: active layer, 452: impurity region, 453: channel formation region, 500: substrate, 501: separation layer, 502: sealing film, 502a: barrier film, 502b: stress relaxation film, 502c: barrier film, 503: semiconductor film, 504: TFT, 505: passivation film, 507: gate insulating film, 508: gate electrode, 510: interlayer insulating film, 513: wiring, 514: wiring, 515: interlayer insulating film, 519: antenna, 521: protective layer, 522: groove, 530: adhesive agent, 531: substrate, 532: adhesive agent, 533: cover member, 540: sealing film, 540a: barrier film, 540b: stress relaxation film, 540c: barrier film, 541: sealing film, 541a: barrier film, 541b: barrier film, 541c: stress relaxation film, 550: wiring, 551: protective layer, 552: groove, 553: adhesive agent, 554: substrate, 555: cover member, 556: sealing film, 556a: barrier film, 556b: stress relaxation film, 556c: barrier film, 557: antenna, 558: adhesive agent, 560: substrate, 561: sealing film, 562: TFT, 563: adhesive agent, 564: base film, 601: TFT, 602: semiconductor film, 603: gate insulating film, 604: gate electrode, 605: passivation film, 606: interlayer insulating film, 607: wiring, 608: antenna, 611: TFT, 612: semiconductor film, 613: gate insulating film, 614: gate electrode, 618: antenna, 701: integrated circuit, 702: antenna, 703: substrate, 704: adhesive agent, 705: cover member, 706: adhesive agent, 707: ID chip, 801: groove, 802: integrated circuit, 803: substrate, 804: separation layer, 805: dashed line, 900: antenna, 901: integrated circuit, 902: antenna coil, 903: capacitor element, 904: modulation circuit, 905: rectification circuit, microprocessor, 907: memory, 908: switch, 909: demodulation circuit